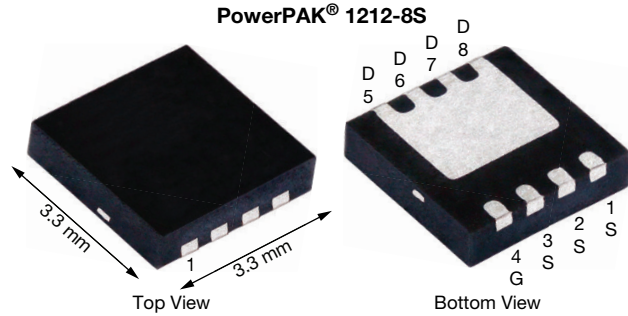


## N-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) (MAX.)	I <sub>D</sub> (A) <sup>a, g</sup>	Q <sub>g</sub> (TYP.)
40	0.00265 at V <sub>GS</sub> = 10 V	60	23 nC
	0.00360 at V <sub>GS</sub> = 4.5 V	60	


**Ordering Information:**

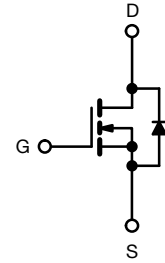
SiSS10DN-T1-GE3 (lead (Pb)-free and halogen-free)

**FEATURES**

- TrenchFET® Gen IV power MOSFET
- Optimized Q<sub>g</sub>, Q<sub>gd</sub>, and Q<sub>gd</sub>/Q<sub>gs</sub> ratio reduces switching related power loss
- 100 % R<sub>g</sub> and UIS tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS**  
 COMPLIANT  
 HALOGEN  
**FREE**
**APPLICATIONS**

- Synchronous rectification
- High power density DC/DC
- VRMs and embedded DC/DC
- Synchronous buck converter
- Load switching
- Battery management



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V <sub>DS</sub>	40	V
Gate-Source Voltage	V <sub>GS</sub>	+20, -16	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	60 <sup>g</sup>
		T <sub>C</sub> = 70 °C	60 <sup>g</sup>
		T <sub>A</sub> = 25 °C	31.7 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	25 <sup>b, c</sup>
Pulsed Drain Current (t = 100 μs)	I <sub>DM</sub>	150	A
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	
		T <sub>A</sub> = 25 °C	4.3 <sup>b, c</sup>
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	30
Single Pulse Avalanche Energy		E <sub>AS</sub>	45
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	57
		T <sub>C</sub> = 70 °C	36
		T <sub>A</sub> = 25 °C	4.8 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	3 <sup>b, c</sup>
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Soldering Recommendations (Peak Temperature) <sup>d, e</sup>		260	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum Junction-to-Ambient <sup>b, f</sup>	t ≤ 10 s	R <sub>thJA</sub>	21	26	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	1.7	2.2	

**Notes**

- Based on T<sub>C</sub> = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The PowerPAK 1212-8S is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 70 °C/W.
- Package limited.

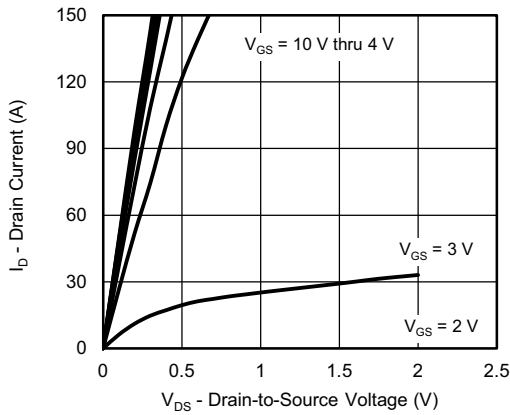
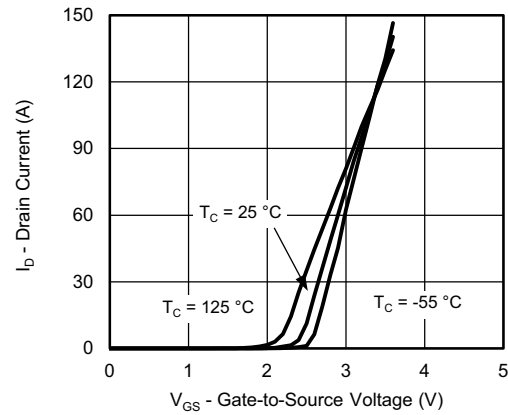
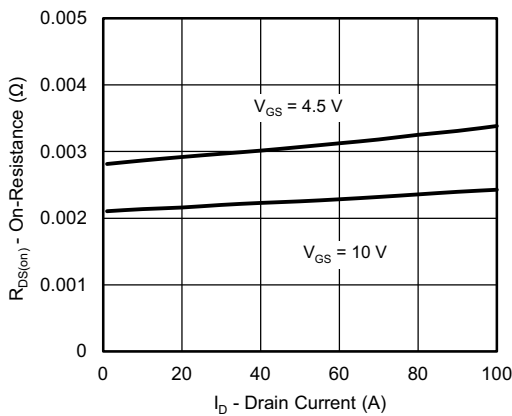
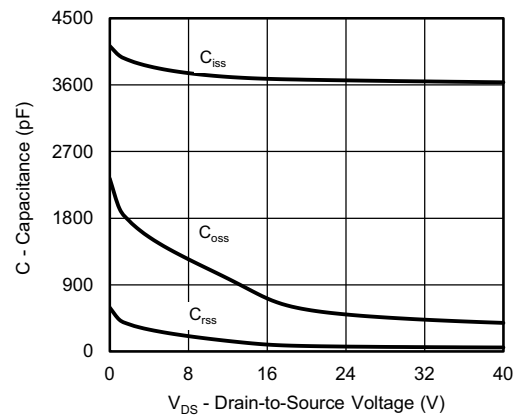
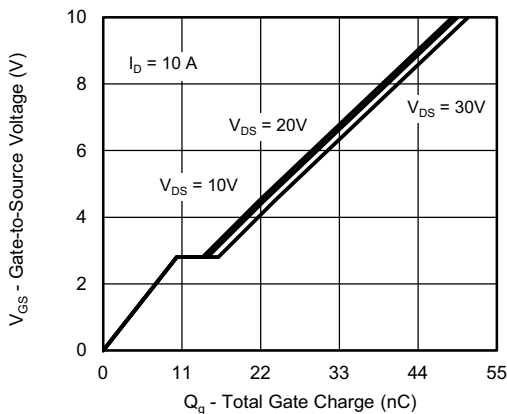
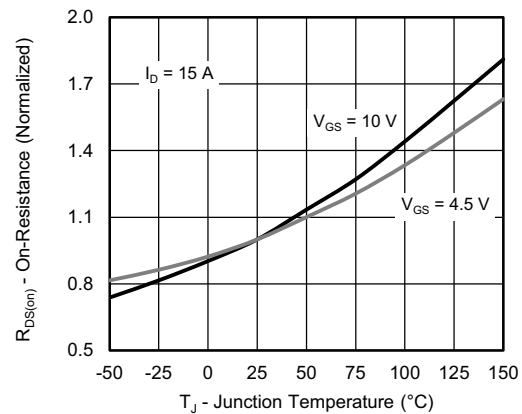


<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	40	-	-	V	
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$	-	24	-	mV/ $^\circ\text{C}$	
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		-	-5.5	-		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.1	-	2.4	V	
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = +20\text{ V}, -16\text{ V}$	-	-	$\pm 100$	nA	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	$\mu\text{A}$	
		$V = 40\text{ V}, V_{DSGS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	-	-	10		
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	30	-	-	A	
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 15\text{ A}$	-	0.00220	0.00265	$\Omega$	
		$V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$	-	0.00300	0.00360		
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 10\text{ V}, I_D = 15\text{ A}$	-	70	-	S	
<b>Dynamic <sup>b</sup></b>							
Input Capacitance	$C_{iss}$	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	-	3750	-	pF	
Output Capacitance	$C_{oss}$		-	560	-		
Reverse Transfer Capacitance	$C_{rss}$		-	72	-		
$C_{rss}/C_{iss}$ Ratio			-	0.019	0.038		
Total Gate Charge	$Q_g$	$V = 20\text{ V}, V_{GS} = 10\text{ V}, I_D = 10\text{ A}$	-	50	75	nC	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 20\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$	-	23	35		
Gate-Drain Charge	$Q_{gd}$		-	10.3	-		
Output Charge	$Q_{oss}$		-	4.3	-		
Gate Resistance	$R_g$	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$	-	37	-	ns	
Turn-On Delay Time	$t_{d(on)}$	$f = 1\text{ MHz}$	0.5	1.2	2.4		
Rise Time	$t_r$	$V_{DD} = 20\text{ V}, R_L = 2\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$	-	10	20		
Turn-Off Delay Time	$t_{d(off)}$		-	19	38		
Fall Time	$t_f$		-	28	56		
Turn-On Delay Time	$t_{d(on)}$		-	7	14		
Rise Time	$t_r$	$V_{DD} = 20\text{ V}, R_L = 2\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$	-	22	44		
Turn-Off Delay Time	$t_{d(off)}$		-	52	100		
Fall Time	$t_f$		-	23	46		
Fall Time	$t_f$		-	10	20		
<b>Drain-Source Body Diode Characteristics</b>							
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$	-	-	51.8		A
Pulse Diode Forward Current ( $t = 100\text{ }\mu\text{s}$ )	$I_{SM}$		-	-	150		
Body Diode Voltage	$V_{SD}$	$I_S = 5\text{ A}$	-	0.73	1.1	V	
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 10\text{ A}, di/dt = 100\text{ A}/\mu\text{s},$ $T_J = 25\text{ }^\circ\text{C}$	-	38	76	ns	
Body Diode Reverse Recovery Charge	$Q_{rr}$		-	33	66	nC	
Reverse Recovery Fall Time	$t_a$		-	20	-	ns	
Reverse Recovery Rise Time	$t_b$		-	18	-		

**Notes**

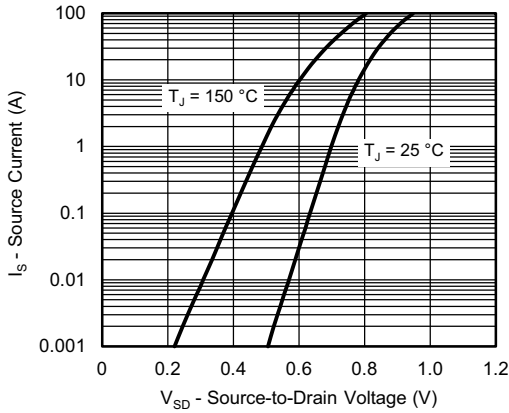
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

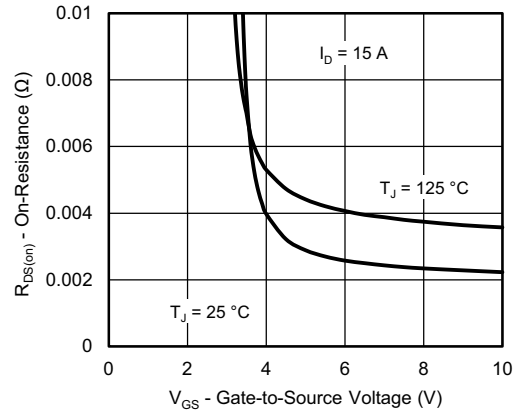
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Output Characteristics**

**Transfer Characteristics**

**On-Resistance vs. Drain Current**

**Capacitance**

**Gate Charge**

**On-Resistance vs. Junction Temperature**



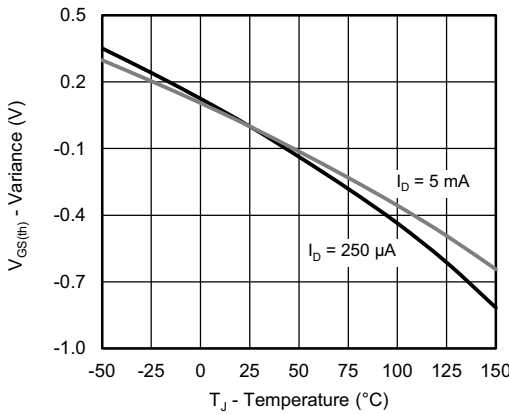
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



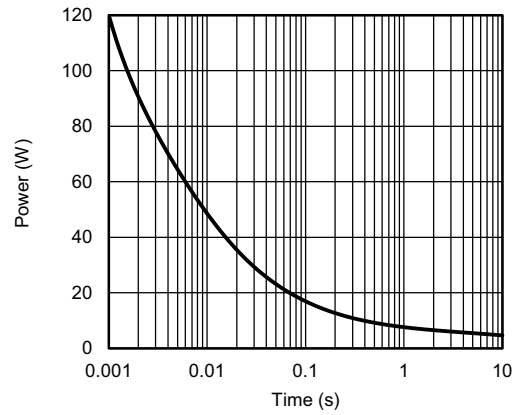
Source-Drain Diode Forward Voltage



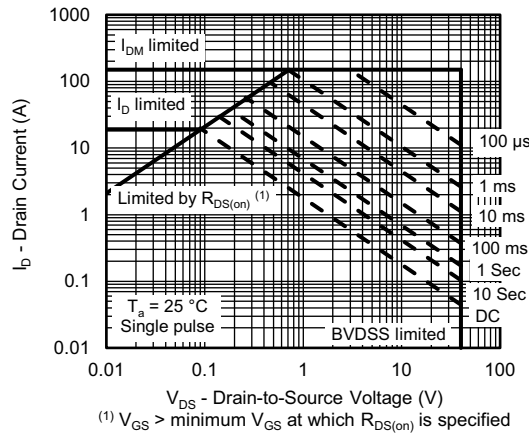
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient

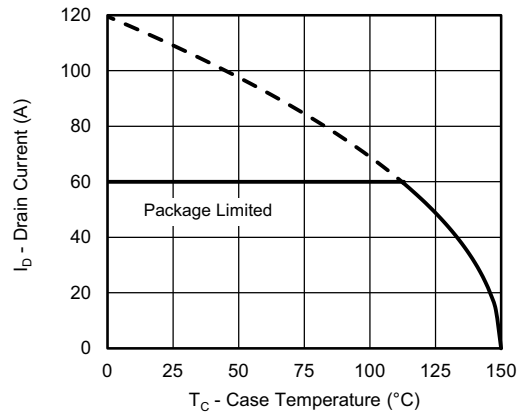


Safe Operating Area

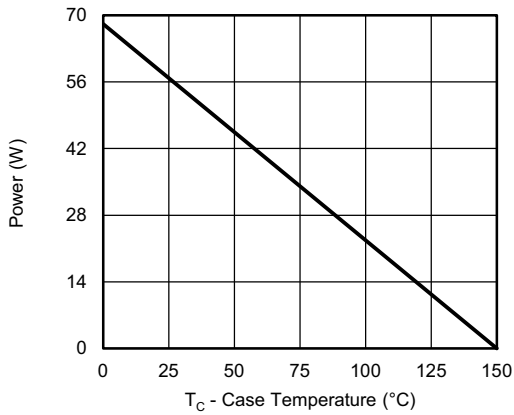
(1) V\_GS > minimum V\_GS at which R\_DS(on) is specified



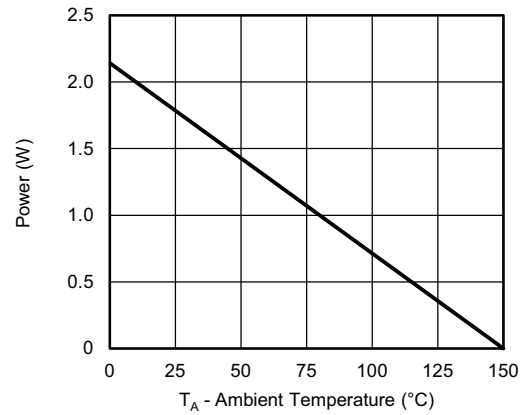
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Current Derating <sup>a</sup>**



**Power, Junction-to-Case**



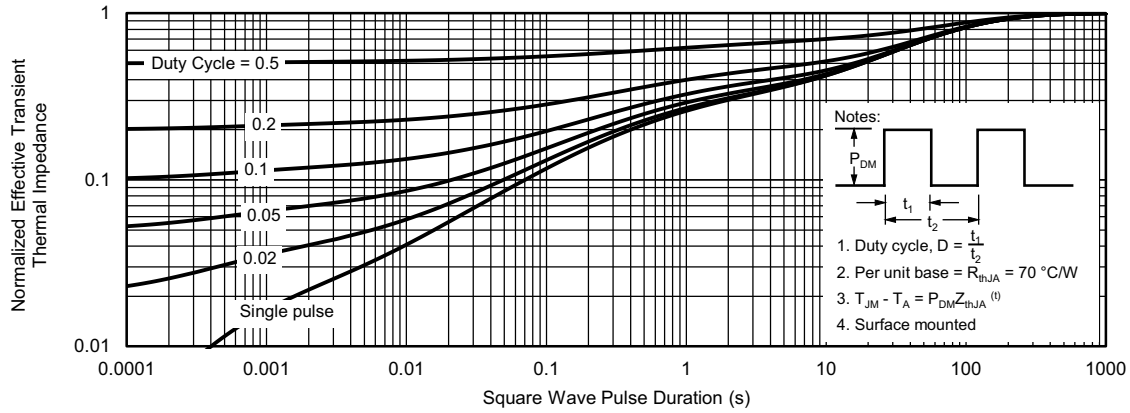
**Power, Junction-to-Ambient**

**Note**

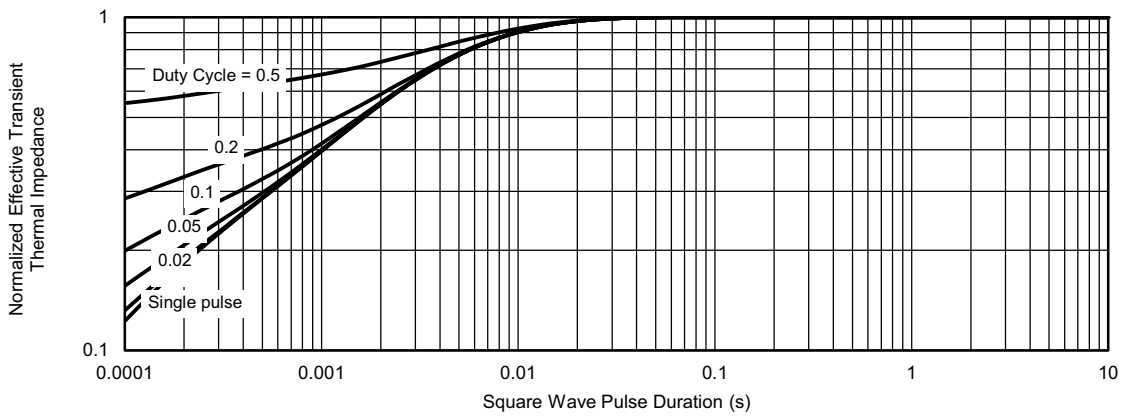
- a. The power dissipation  $P_D$  is based on  $T_J$  (max.) = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Case**

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## Case Outline for PowerPAK® 1212-8S



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.67	0.75	0.83	0.026	0.030	0.033
A1	0.00	-	0.05	0.000	-	0.002
A3	0.20 ref.			0.008 ref		
b	0.25	0.30	0.35	0.010	0.012	0.014
D	3.20	3.30	3.40	0.126	0.130	0.134
D1	2.15	2.25	2.35	0.085	0.089	0.093
E	3.20	3.30	3.40	0.126	0.130	0.134
E1	1.60	1.70	1.80	0.063	0.067	0.071
e	0.65 bsc.			0.026 bsc.		
K	0.76 ref.			0.030 ref.		
K1	0.41 ref.			0.016 ref.		
L	0.33	0.43	0.53	0.013	0.017	0.021
Z	0.525 ref.			0.021 ref.		

ECN: C20-0862-Rev. B, 20-Jul-2020  
DWG: 6008

## RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads  
Dimensions in Inches/(mm)

[Return to Index](#)





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